BJT - Bipolar Junction Transistor Both operation same. Reason: (1) npn Fast 0.2 How many terminal (2) Rmallin Size and how many Junction? Because: Mobility of e are greater as 3 terminal and Two Compared to hole Junction or seen from above Fig. mobility. How many configuration possible: mobility of Mobility 3 Configuration possible. holex -> Common Emitter Ly Common Base

Ly Common Collector

0.4 which configuration is best -

Common Emitter Configuration mostly Used. Have high power gain and weful for amplification.

Q.5

N+

P

N

Oc

B

Ji JJ2

OB

Size: 6>E7B.

Dobing E>C>B

Q.6 Symmetric device or Assymetric

Osthey have we can not interchange different Rize and doping profile Emitter, Base, Collector

De can apply External voltage to bias I, and

To Junction. > Base on I and I Junction biasing

we can make our BJT tooperate in Four Modes

I - Mode FB RB > Active Mode > used toramplif

II - Mode FB FB > Saturation Mode - Jused for switch

III - Mode RB RB > Cut of smooth of the full of the RB > Revence active > No such useful application.

B>1

$$\beta = \frac{I_c}{I_B} \Rightarrow I_c = \beta I_B$$

characteristic
of this

Current gain (B)

$$B = \frac{I_c}{I_B} \Rightarrow I_c = \beta I$$

$$I_E > I_c > I_B$$

$$\zeta = \frac{\mathcal{I}^{\mathcal{B}}}{\mathcal{I}^{\mathcal{E}}}$$

$$I \in = \chi I_B$$
.

> Very important Mostly Used.

